

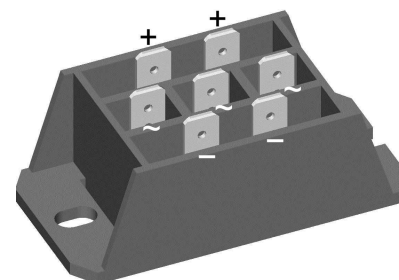
Standard Rectifier Module

3~ Rectifier	
V_{RRM}	= 1600 V
I_{DAV}	= 60 A
I_{FSM}	= 500 A

3~ Rectifier Bridge

Part number

VUO50-16NO3



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: FO-F

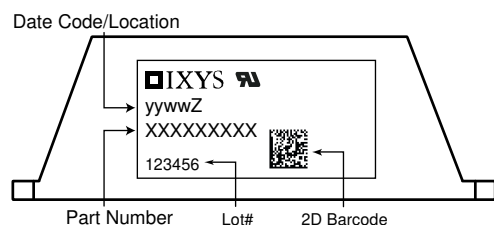
- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- 1/4" fast-on terminals
- Easy to mount with two screws
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
I_R	reverse current	$V_R = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			40	μA
		$V_R = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			1.5	mA
V_F	forward voltage drop	$I_F = 20\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.07	V
		$I_F = 60\text{ A}$				1.32	V
		$I_F = 20\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.98	V
		$I_F = 60\text{ A}$				1.30	V
I_{DAV}	bridge output current	$T_C = 110^{\circ}\text{C}$ rectangular	$T_{VJ} = 150^{\circ}\text{C}$ $d = \frac{1}{3}$			60	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.78	V
r_F	slope resistance					8.5	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.4		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				80	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			500	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			540	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			425	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			460	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1.25	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.22	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			905	A ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			880	A ² s
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$			25		pF

Package FO-F				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal				100	A	
T _{VJ}	virtual junction temperature			-40		150	°C	
T _{op}	operation temperature			-40		125	°C	
T _{stg}	storage temperature			-40		125	°C	
Weight					45		g	
M _D	mounting torque			2		2.5	Nm	
d _{Spp/App}	creepage distance on surface striking distance through air	terminal to terminal	18.0	6.0			mm	
d _{Spb/Apb}		terminal to backside	26.0	20.0			mm	
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		3600			V
		t = 1 minute			3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO50-16NO3	VUO50-16NO3	Box	10	426113

Equivalent Circuits for Simulation

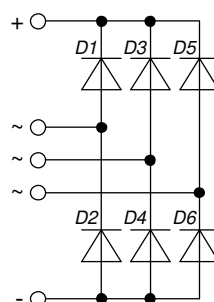
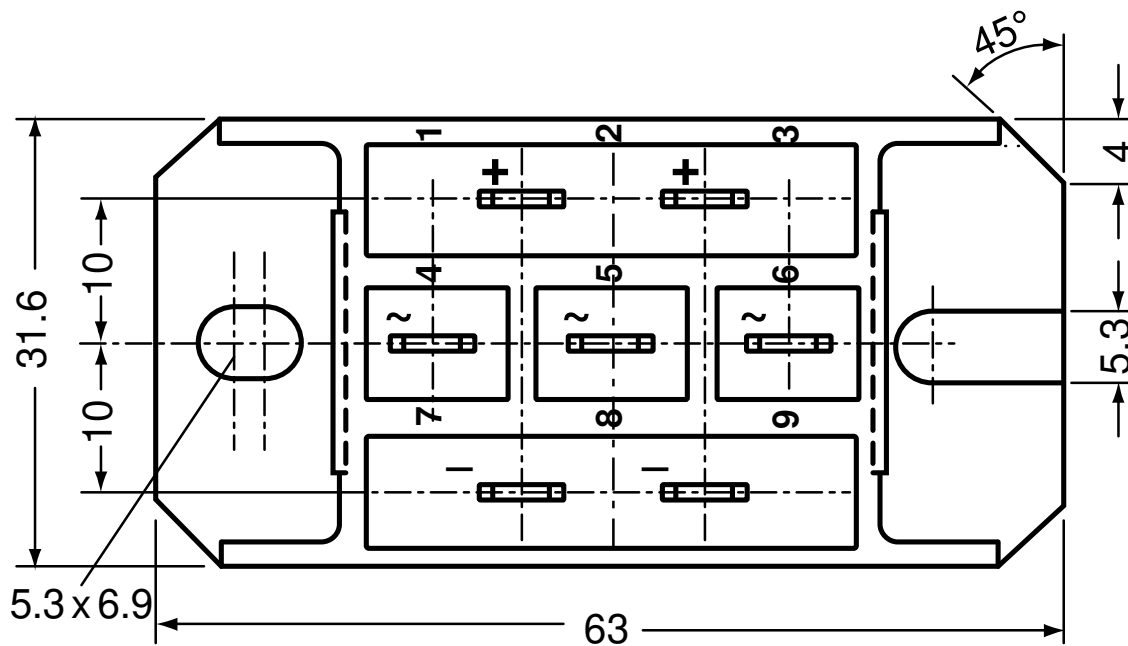
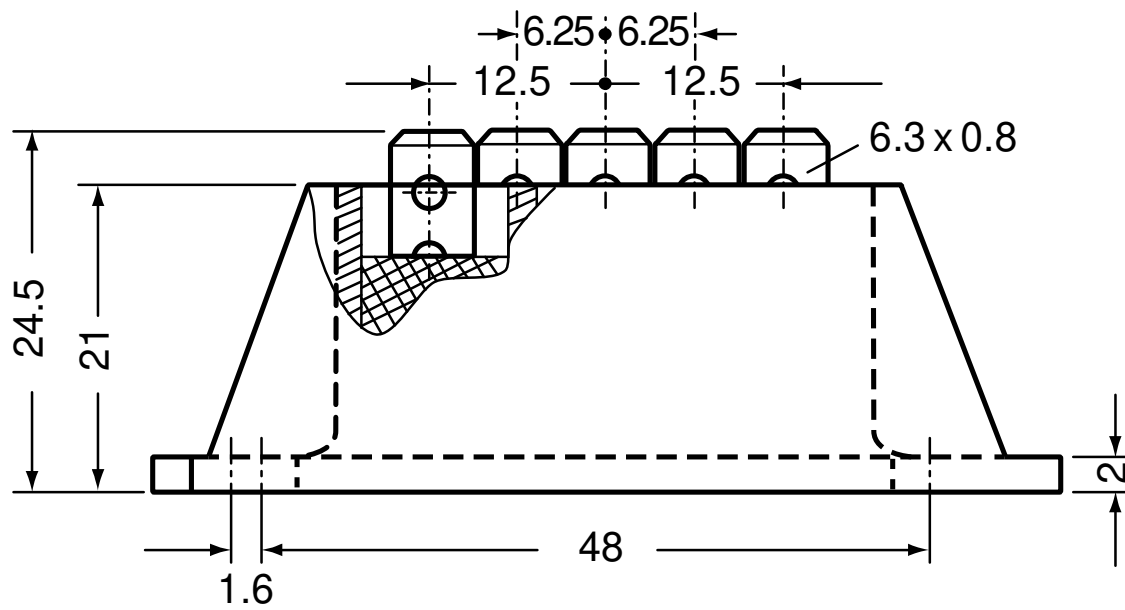
* on die level

$T_{VJ} = 150^{\circ}\text{C}$

			Rectifier	
$V_{0\max}$	threshold voltage	0.78		V
$R_{0\max}$	slope resistance *	7.3		mΩ



Outlines FO-F



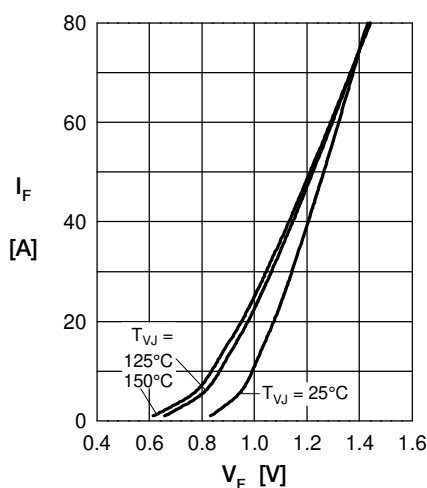
Rectifier


Fig. 1 Forward current vs. voltage drop per diode

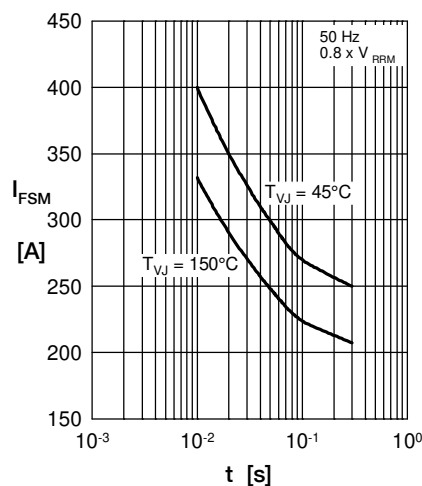


Fig. 2 Surge overload current vs. time per diode

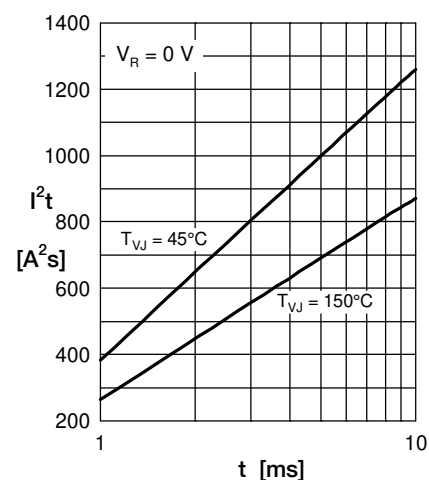


Fig. 3 I^2t vs. time per diode

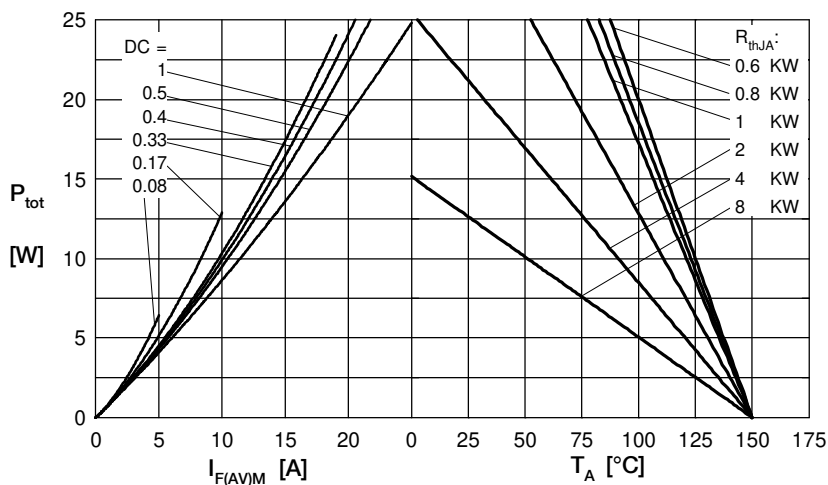


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

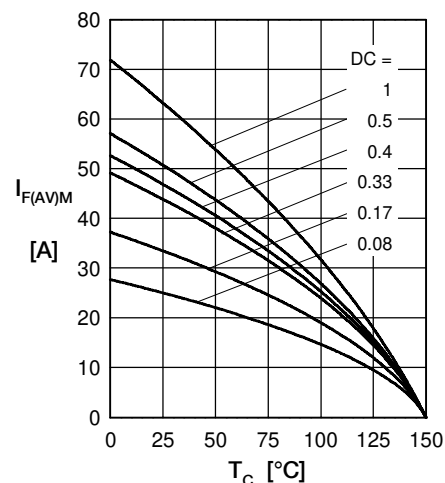


Fig. 5 Max. forward current vs. case temperature per diode

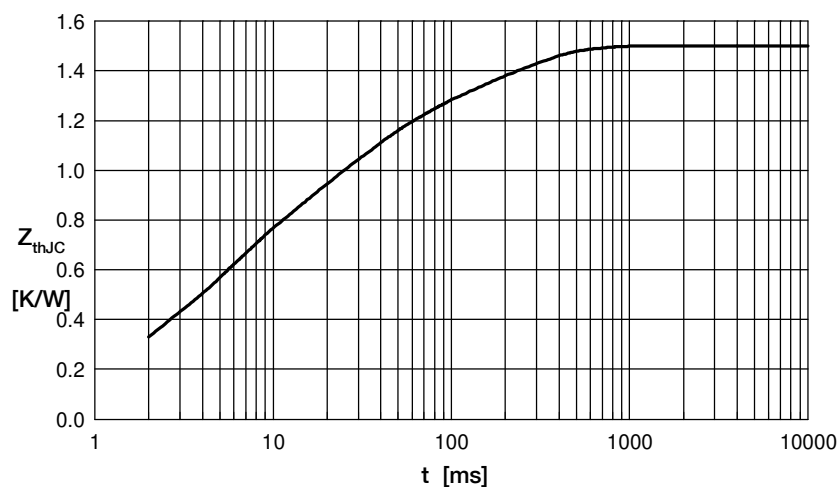


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.0607	0.00040
2	0.1330	0.00256
3	0.4305	0.00450
4	0.5130	0.02420
5	0.3628	0.18000